
HM62W864 Series

65536-word \times 8-bit Low Voltage Operation CMOS Static RAM

HITACHI

ADE-203-281B (Z)
Rev. 2.0
Jul. 25, 1995

Description

The Hitachi HM62W864 is a CMOS static RAM organized 64-kword \times 8-bit. It realizes higher density, higher performance and low power consumption by employing 0.8 μ m Hi-CMOS process technology. It offers low power standby power dissipation; therefore, it is suitable for battery backup systems. The device, packaged in a 525-mil SOP (460-mil body SOP) and a 8 \times 20 mm TSOP with thickness of 1.2 mm, is available for high density mounting. TSOP package is suitable for cards.

Features

- Low voltage operation SRAM
Single 3.0 V to 3.6 V supply
- High speed
— Fast access time: 85 ns (max)
- Low power
— Standby: 0.66 μ W (typ)
- Completely static memory
No clock or timing strobe required
- Equal access and cycle times
- Common data input and output
Three state output
- Directly LVTTTL compatible
All inputs and outputs
- Capability of battery backup operation
2 chip selection for battery backup

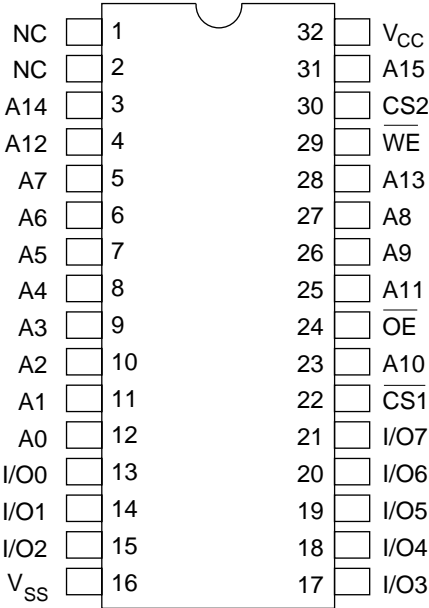
Ordering Information

Type No.	Access Time	Package
HM62W864LFP-8	85 ns	525-mil 32-pin plastic SOP (FP-32D)
HM62W864LT-8	85 ns	8 mm \times 20 mm 32-pin TSOP (normal type) (TFP-32D)

HM62W864 Series

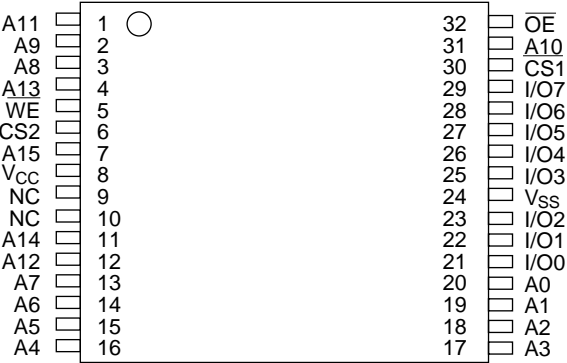
Pin Arrangement

HM62W864LFP Series



(Top view)

HM62W864LFP Series

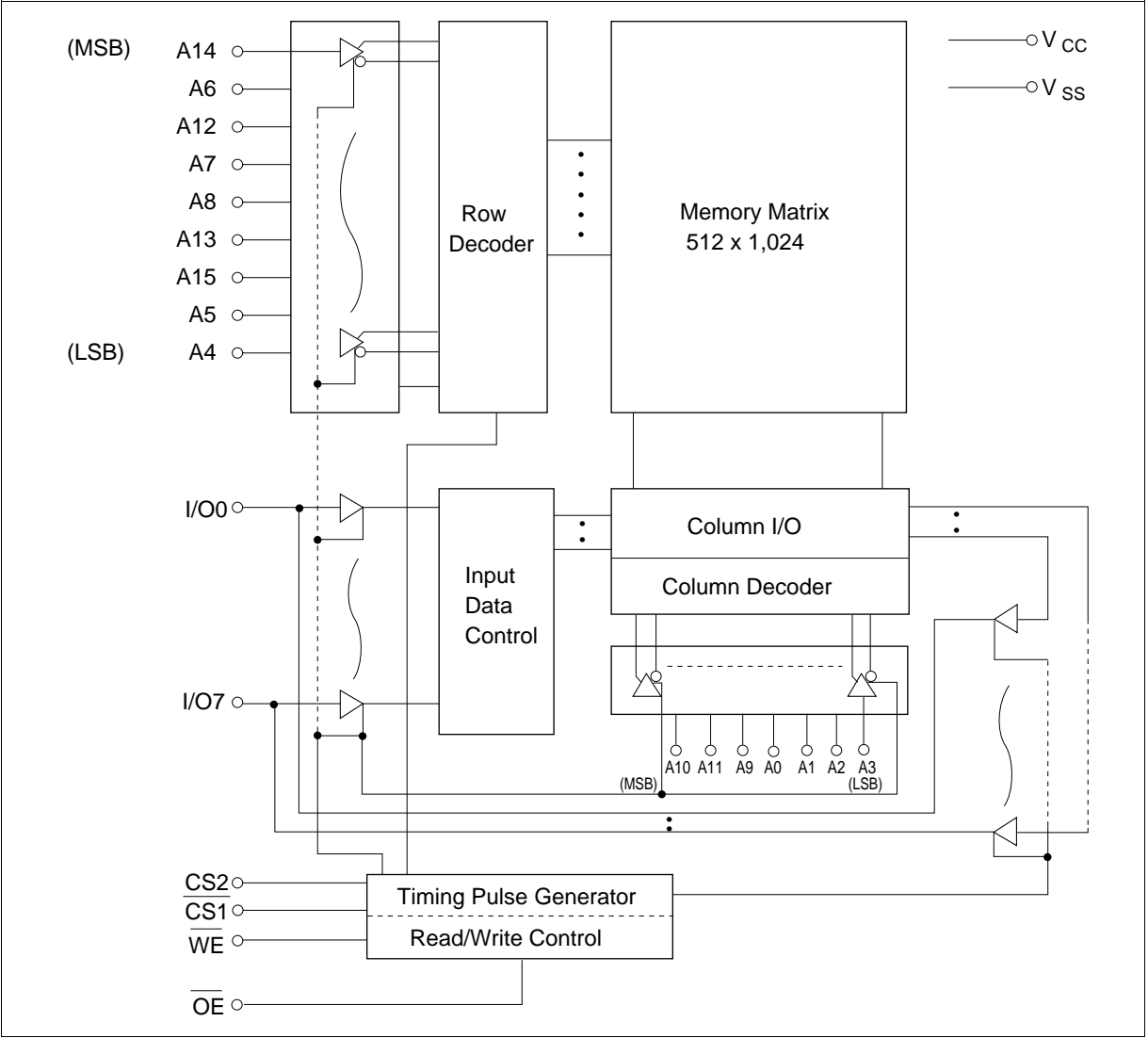


(Top view)

Pin Description

Pin Name	Function
A0 to A15	Address
I/O0 to I/O7	Data input/output
$\overline{\text{CS1}}$	Chip select 1
CS2	Chip select 2
$\overline{\text{WE}}$	Write enable
$\overline{\text{OE}}$	Output enable
NC	No connection
V _{cc}	Power supply
V _{ss}	Ground

Block Diagram



Function Table

CS1	CS2	OE	WE	Mode	V _{CC} Current	I/O Pin	Ref. Cycle
H	X	X	X	Not selected	I _{SB} , I _{SB1}	High-Z	—
X	L	X	X	Not selected	I _{SB} , I _{SB1}	High-Z	—
L	H	H	H	Output disable	I _{CC}	High-Z	—
L	H	L	H	Read	I _{CC}	Dout	Read cycle (1) to (3)
L	H	H	L	Write	I _{CC}	Din	Write cycle (1)
L	H	L	L	Write	I _{CC}	Din	Write cycle (2)

Note: X: High or Low

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage ^{*1}	V _{CC}	−0.5 to +4.6	V
Terminal voltage ^{*1}	V _T	−0.5 ^{*2} to V _{CC} + 0.5 ^{*3}	V
Power dissipation	P _T	1.0	W
Operating temperature	Topr	0 to +70	°C
Storage temperature	Tstg	−55 to +125	°C
Storage temperature under bias	Tbias	−10 to +85	°C

- Notes: 1. Relative to V_{SS}
2. V_T min: −3.0 V for pulse half-width ≤ 50 ns
3. Maximum voltage is 4.6V

Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V _{CC}	3.0	3.3	3.6	V
	V _{SS}	0	0	0	V
Input high (logic 1) voltage	V _{IH}	2.0	—	V _{CC} + 0.3	V
Input low (logic 0) voltage	V _{IL}	−0.3 ^{*1}	—	0.8	V

Note: 1. V_{IL} min: −3.0 V for pulse half-width ≤ 50 ns

DC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Min	Typ ^{*1}	Max	Unit	Test conditions
Input leakage current	$ I_{LI} $	—	—	1	μA	$V_{SS} \leq V_{in} \leq V_{CC}$
Output leakage current	$ I_{LO} $	—	—	1	μA	$\overline{CS1} = V_{IH}$ or $CS2 = V_{IL}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$, $V_{SS} \leq V_{I/O} \leq V_{CC}$
Operating power supply current	I_{CC}	—	—	15	mA	$\overline{CS1} = V_{IL}$, $CS2 = V_{IH}$, Others = V_{IH}/V_{IL} , $I_{I/O} = 0\text{ mA}$
Average operating power supply current	I_{CC1}	—	—	35	mA	Min cycle, duty = 100%, $\overline{CS1} = V_{IL}$, $CS2 = V_{IH}$ Others = V_{IH}/V_{IL} , $I_{I/O} = 0\text{ mA}$
	I_{CC2}	—	10	15	mA	Cycle time = $1\text{ }\mu\text{s}$, duty = 100%, $I_{I/O} = 0\text{ mA}$, $\overline{CS1} \leq V_{IL}$, $CS2 \geq V_{IH}$, Others = V_{IH}/V_{IL} , $V_{IH} \geq V_{CC} - 0.2\text{ V}$, $0\text{ V} \leq V_{IL} \leq 0.2\text{ V}$
Standby power supply current	I_{SB}	—	0.1	1	mA	(1) or (2) (1) $\overline{CS1} = V_{IH}$, $CS2 = V_{IH}$ (2) $CS2 = V_{IL}$
	I_{SB1}	—	0.2	50	μA	$0\text{ V} \leq V_{in} \leq V_{CC}$, (1) or (2) (1) $\overline{CS1} \geq V_{CC} - 0.2\text{ V}$, $CS2 \geq V_{CC} - 0.2\text{ V}$ (2) $0\text{ V} \leq CS2 \leq 0.2\text{ V}$
Output low voltage	V_{OL}	—	—	0.4	V	$I_{OL} = 2.0\text{ mA}$
		—	—	0.2	V	$I_{OL} = 100\text{ }\mu\text{A}$
Output high voltage	V_{OH}	$V_{CC} - 0.2$	—	—	V	$I_{OH} = -100\text{ }\mu\text{A}$
		2.4	—	—	V	$I_{OH} = -2.0\text{ mA}$

Note: 1. Typical values are at $V_{CC} = 3.3\text{ V}$, $T_a = +25^\circ\text{C}$ and not guaranteed.

Capacitance ($T_a = 25^\circ\text{C}$, $f = 1.0\text{ MHz}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Input capacitance ^{*1}	C_{in}	—	—	5	pF	$V_{in} = 0\text{ V}$
I/O Pin capacitance ^{*1}	$C_{I/O}$	—	—	8	pF	$V_{I/O} = 0\text{ V}$

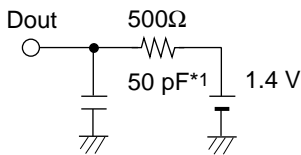
Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics (Ta = 0 to +70°C, VCC = 3.3 V ± 0.3 V, unless otherwise noted.)

Test Conditions

- Input pulse levels: 0.4 V to 2.4 V
- Input rise and fall time: 5 ns
- Input timing reference level: 1.4 V
- Output timing reference level: 0.8 V/2.0 V

Output Load



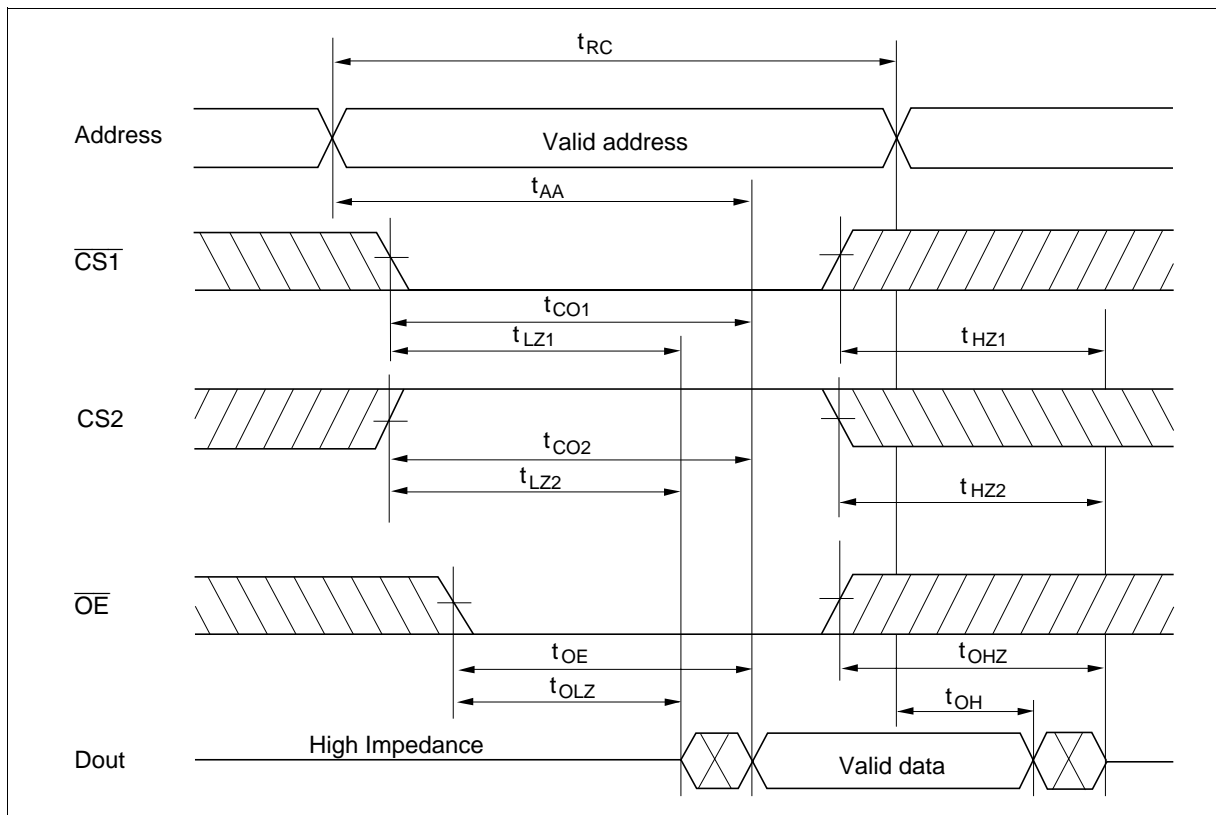
Note 1. Including scope & jig

Read Cycle

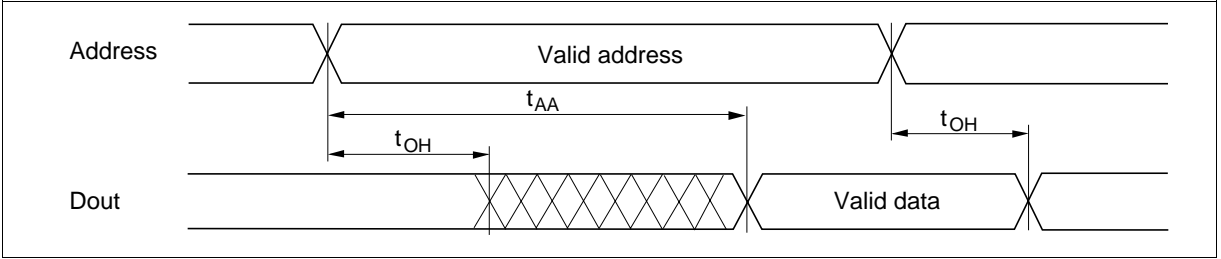
Parameter	Symbol	HM62W864-8		Unit	Notes
		Min	Max		
Read cycle time	t _{RC}	85	—	ns	
Address access time	t _{AA}	—	85	ns	
Chip select access time	$\overline{\text{CS1}}$ t _{CO1}	—	85	ns	
	CS2 t _{CO2}	—	85	ns	
Output enable to output valid	t _{OE}	—	45	ns	
Chip selection to output in low-Z	$\overline{\text{CS1}}$ t _{LZ1}	10	—	ns	2
	CS2 t _{LZ2}	10	—	ns	2
Output enable to output in low-Z	t _{OLZ}	5	—	ns	2
Chip deselection in output in high-Z	$\overline{\text{CS1}}$ t _{HZ1}	0	30	ns	1, 2
	CS2 t _{HZ2}	0	30	ns	1, 2
Output disable to output in high-Z	t _{OHZ}	0	30	ns	1, 2
Output hold from address change	t _{OH}	10	—	ns	

- Notes: 1. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
2. This parameter is sampled and not 100% tested.

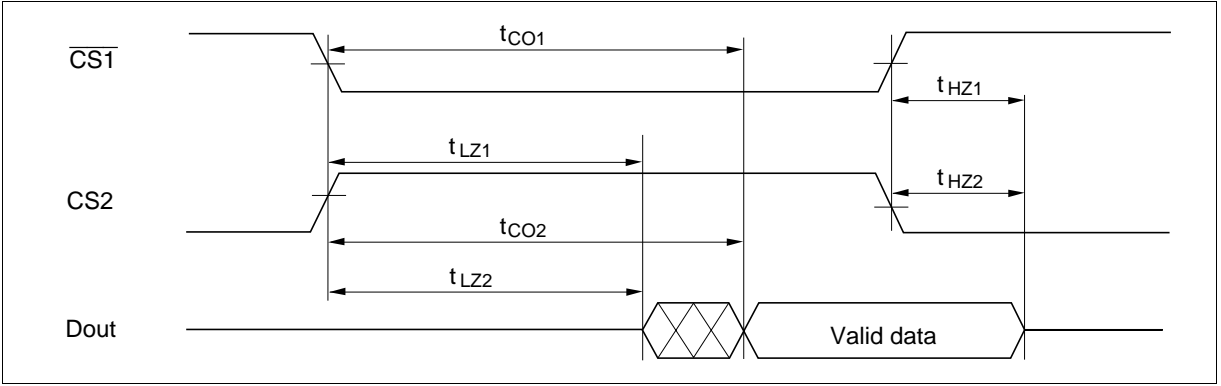
Read Timing Waveform (1) ($\overline{WE} = V_{IH}$)



Read Timing Waveform (2) ($\overline{WE} = V_{IH}$)



Read Timing Waveform (3) ($\overline{WE} = V_{IH}$)

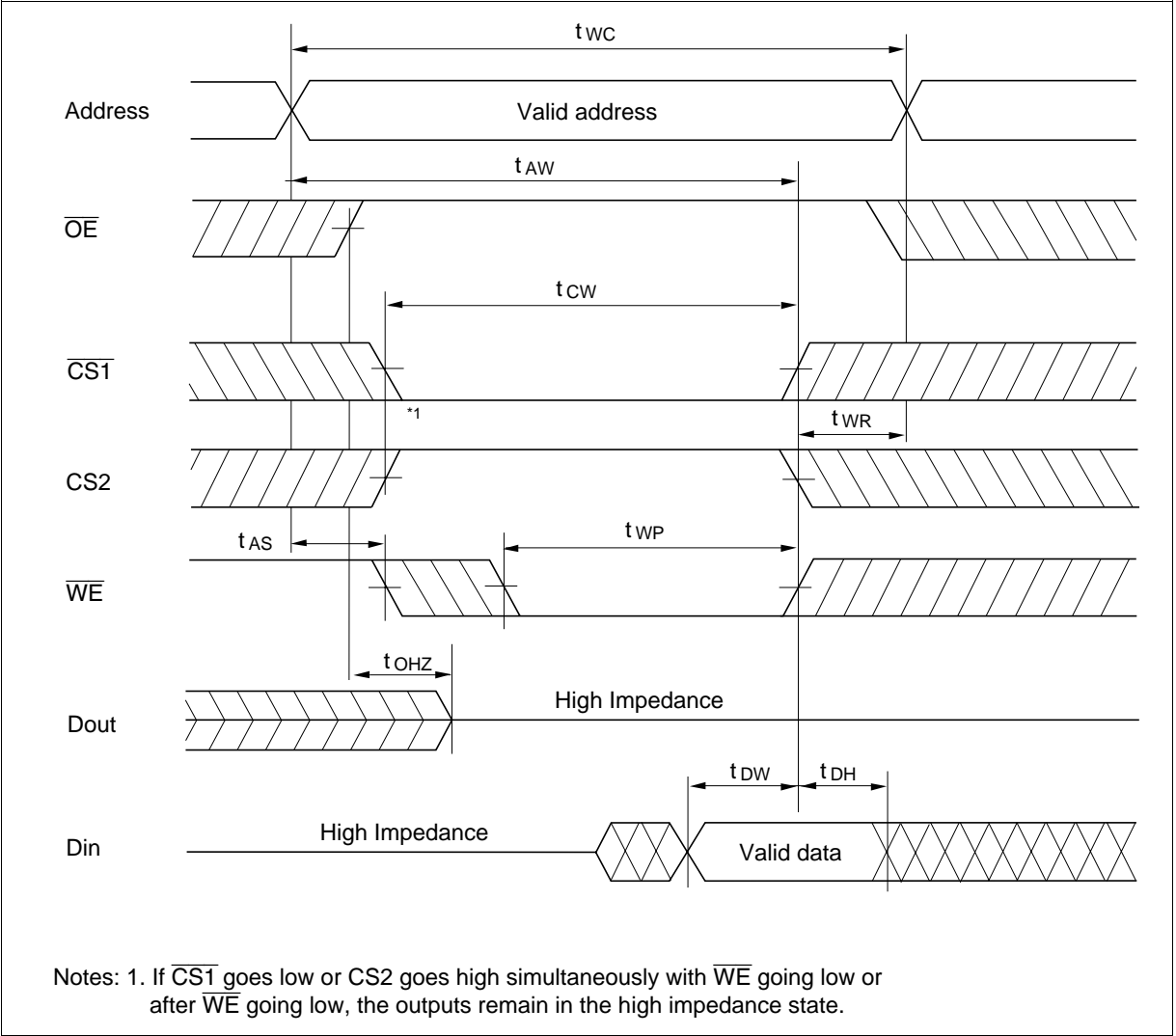


Write Cycle

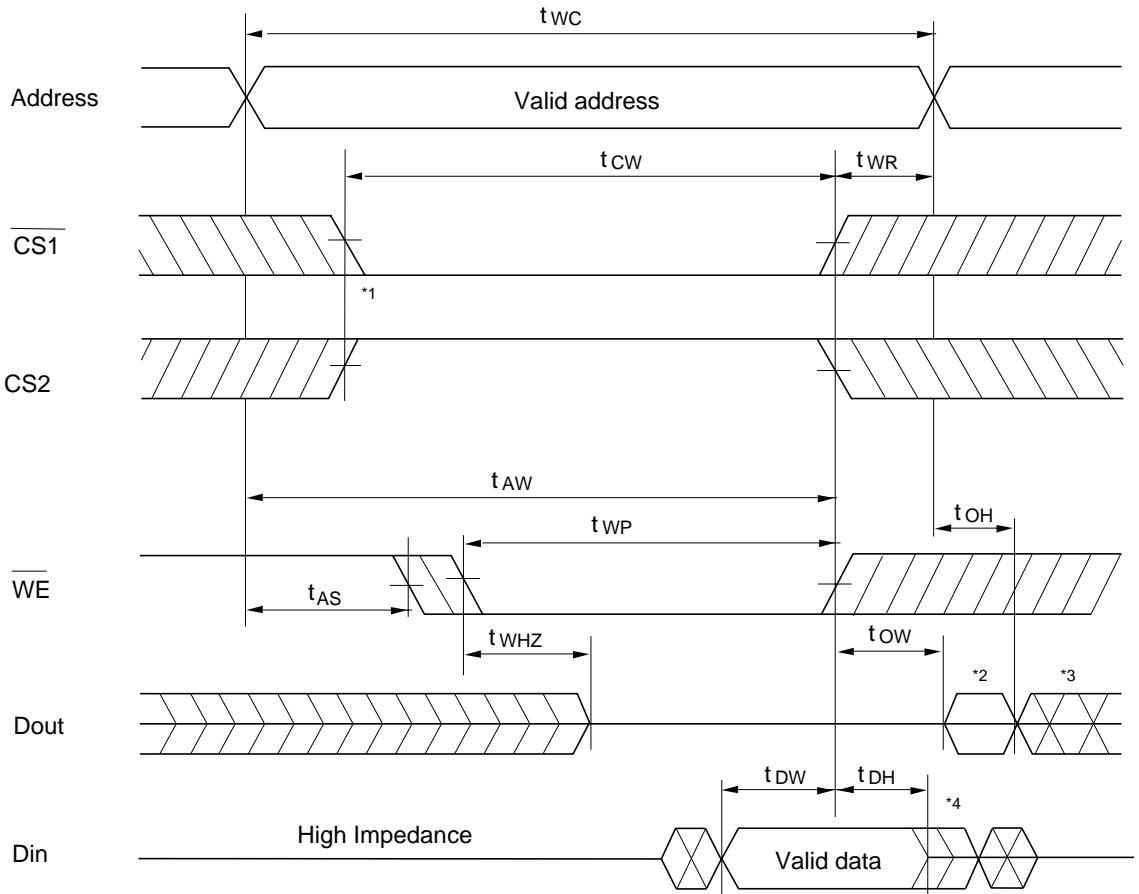
Parameter	Symbol	HM62W864-8		Unit	Notes
		Min	Max		
Write cycle time	t_{WC}	85	—	ns	
Chip selection to end of write	t_{CW}	75	—	ns	4
Address setup time	t_{AS}	0	—	ns	5
Address valid to end of write	t_{AW}	75	—	ns	
Write pulse width	t_{WP}	55	—	ns	3, 8
Write recovery time	t_{WR}	0	—	ns	6
Write to output in high-Z	t_{WHZ}	0	30	ns	1, 2, 7
Data to write time overlap	t_{DW}	35	—	ns	
Data hold from write time	t_{DH}	0	—	ns	
Output active from end of write	t_{OW}	5	—	ns	2
Output disable to output in high-Z	t_{OHZ}	0	30	ns	1, 2, 7

- Notes:
1. t_{WHZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 2. This parameter is sampled and not 100% tested.
 3. A write occurs during the overlap of a low $\overline{CS1}$, a high CS2 and a low \overline{WE} . A write begins at the latest transition among $\overline{CS1}$ going low, CS2 going high, and \overline{WE} going low. A write ends at the earliest transition among $\overline{CS1}$ going high, CS2 going low, and \overline{WE} going high. t_{WP} is measured from the beginning of write to the end of write.
 4. t_{CW} is measured from the later of $\overline{CS1}$ going low or CS2 going high to the end of write.
 5. t_{AS} is measured from the address valid to the beginning of write.
 6. t_{WR} is measured from the earliest of $\overline{CS1}$ or \overline{WE} going high or CS2 going low to the end of write cycle.
 7. During this period, I/O pin are in the output state; therefore, the input signals of the opposite phase to the outputs must not be applied.
 8. In the write cycle with \overline{OE} low fixed, t_{WP} must satisfy the following equation to avoid a problem of data bus contention, $t_{WP} \geq t_{WHZ} \text{ max} + t_{DW} \text{ min}$.

Write Timing Waveform (1) ($\overline{\text{OE}}$ Clock)



Write Timing Waveform (2) ($\overline{\text{OE}}$ Low Fixed)



- Notes: 1. If $\overline{\text{CS1}}$ goes low or $\overline{\text{CS2}}$ goes high simultaneously with $\overline{\text{WE}}$ going low or after $\overline{\text{WE}}$ going low, the outputs remain in the high impedance state.
 2. Dout is the same phase of the latest written data in this write cycle.
 3. Dout is the read data of next address.
 4. If $\overline{\text{CS1}}$ is low and $\overline{\text{CS2}}$ is high during this period, I/O pins are in the output state. Therefore, the input signals of opposite phase to the outputs must not be applied to them.

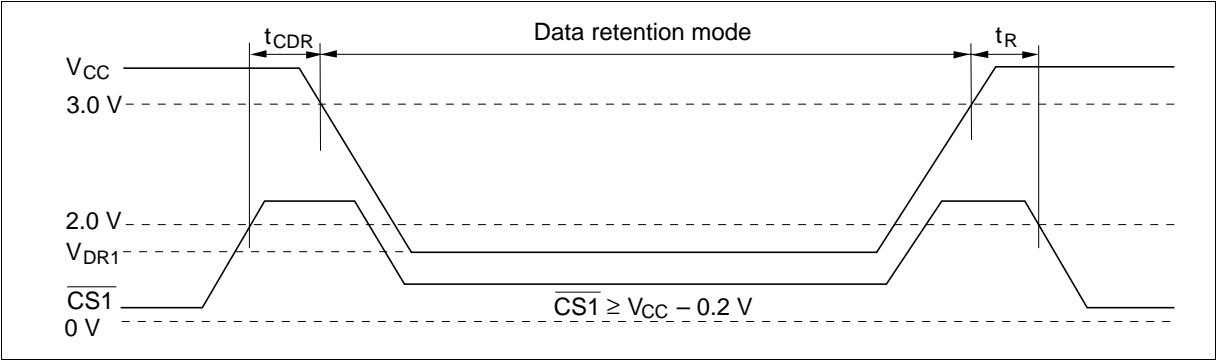
Low V_{CC} Data Retention Characteristics (Ta = 0 to +70°C)

This characteristics is guaranteed only for L-version.

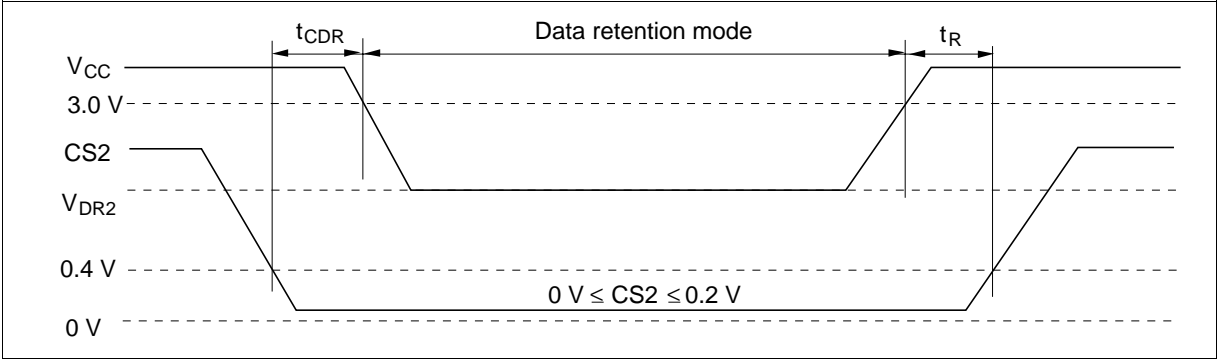
Parameter	Symbol	Min	Typ ^{*1}	Max	Unit	Test conditions ^{*4}
V _{CC} for data retention	V _{DR}	2.0	—	3.6	V	0 V ≤ Vin ≤ V _{CC} , (1) or (2) (1) $\overline{CS1} \geq V_{CC} - 0.2 \text{ V}$, CS2 ≥ V _{CC} - 0.2 V (2) 0 V ≤ CS2 ≤ 0.2 V
Data retention current	I _{CCDR}	—	0.1	30 ^{*2}	μA	V _{CC} = 3.0 V, 0 V ≤ Vin ≤ V _{CC} , (1) or (2) (1) $\overline{CS1} \geq V_{CC} - 0.2 \text{ V}$, CS2 ≥ V _{CC} - 0.2 V (2) 0 V ≤ CS2 ≤ 0.2 V
Chip deselect to data retention time	t _{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t _R	t _{RC} ^{*3}	—	—	ns	

Notes: 1. Typical values are at V_{CC} = 3.0 V, Ta = 25°C and not guaranteed.
2. 20 μA max at Ta = 0 to 40°C.
3. t_{RC} = Read cycle time.
4. CS2 controls address buffer, \overline{WE} buffer, $\overline{CS1}$ buffer, \overline{OE} buffer, and Din buffer. If CS2 controls data retention mode, Vin levels (address, \overline{WE} , \overline{OE} , $\overline{CS1}$, I/O) can be in the high impedance state. If $\overline{CS1}$ controls data retention mode, CS2 must be CS2 ≥ V_{CC} - 0.2 V or 0 V ≤ CS2 ≤ 0.2 V. The other input levels (address, \overline{WE} , \overline{OE} , I/O) can be in the high impedance state.

Low V_{CC} Data Retention Timing Waveform (1) ($\overline{CS1}$ Controlled)



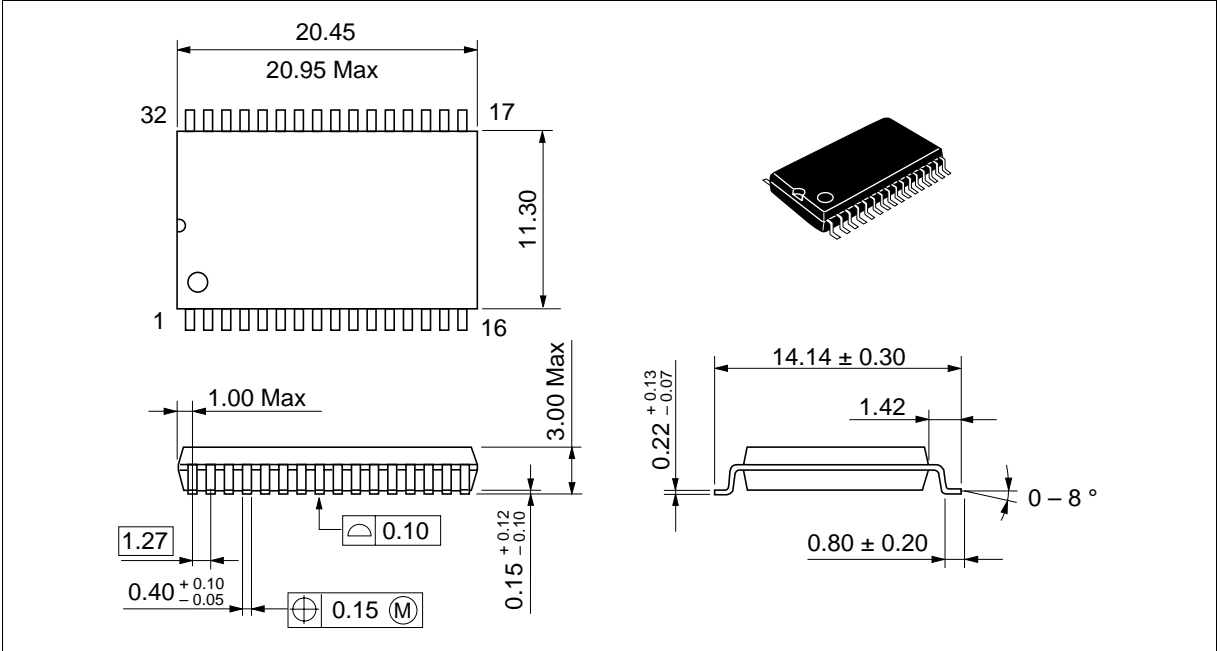
Low V_{CC} Data Retention Timing Waveform (2) (CS2 Controlled)



Package Dimensions

HM62W864LFP Series (FP-32D)

Unit: mm



HM62W864 Series

HM62W864LT Series (TFP-32D)

Unit: mm

